

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Planar PIN diode in a SOD882T leadless ultra small plastic SMD package.

#### 1.2 Features

- High voltage, current controlled RF resistor for RF attenuators and switches
- Low diode capacitance
- Low forward resistance
- Very low series inductance
- For applications up to 3 GHz

### 1.3 Applications

RF attenuators and switches

### 2. Pinning information

Table 1. Discrete pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode	Transparent top view	sym006

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BAP64LX	-	leadless ultra small plastic package; 2 terminals; body 1.0 $\times$ 0.6 $\times$ 0.4 mm	SOD882T			





### 4. Marking

Table 3. Marking

Type number	Marking code
BAP64LX	LE

# 5. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage		-	60	V
I <sub>F</sub>	forward current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} = 90  ^{\circ}C$	-	150	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

### 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		56	K/W

### 7. Characteristics

Table 6. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	I <sub>F</sub> = 100 mA	-	0.95	1.1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V	-	-	100	nA
C <sub>d</sub>	diode capacitance	see Figure 1; f = 1 MHz;				
		$V_R = 0 V$	-	0.48	-	рF
		V <sub>R</sub> = 1 V	-	0.34	-	рF
		V <sub>R</sub> = 20 V	-	0.17	0.30	pF
$r_D$	diode forward resistance	see Figure 2; f = 100 MHz;				
		$I_F = 0.5 \text{ mA}$	-	31	50	Ω
		I <sub>F</sub> = 1 mA	-	16	26	Ω
		I <sub>F</sub> = 10 mA	-	2.6	4.4	Ω
		I <sub>F</sub> = 100 mA	-	0.9	1.5	Ω
ISL	isolation	see Figure 3; V <sub>R</sub> = 0 V;				
		f = 900 MHz	-	22	-	dB
		f = 1800 MHz	-	16	-	dB
		f = 2450 MHz	-	14	-	dB
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Table 6. Characteristics ...continued

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L <sub>ins</sub>	insertion loss	see Figure 4; $I_F = 0.5 \text{ mA}$ ;				
		f = 900 MHz	-	1.22	-	dB
		f = 1800 MHz	-	1.21	-	dB
		f = 2450 MHz	-	1.22	-	dB
L <sub>ins</sub>	insertion loss	see Figure 4; I <sub>F</sub> = 1 mA;				
		f = 900 MHz	-	0.22	-	dB
		f = 1800 MHz	-	0.23	-	dB
		f = 2450 MHz	-	0.24	-	dB
L <sub>ins</sub>	insertion loss	see Figure 4; I <sub>F</sub> = 10 mA;				
		f = 900 MHz	-	0.12	-	dB
		f = 1800 MHz	-	0.14	-	dB
		f = 2450 MHz	-	0.15	-	dB
L <sub>ins</sub>	insertion loss	see Figure 4; I <sub>F</sub> = 100 mA;				
		f = 900 MHz	-	0.09	-	dB
		f = 1800 MHz	-	0.10	-	dB
		f = 2450 MHz	-	0.11	-	dB
τ∟	charge carrier life time	when switched from I $_{\!F}$ = 10 mA to I $_{\!R}$ = 6 mA; R $_{\!L}$ = 100 $\Omega;$ measured at I $_{\!R}$ = 3 mA	-	1.0	-	μs
L <sub>S</sub>	series inductance	$I_F = 100 \text{ mA}; f = 100 \text{ MHz}$	-	0.4	-	nΗ

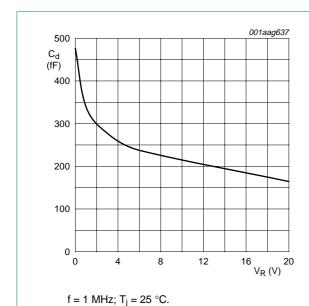


Fig 1. Diode capacitance as a function of reverse voltage; typical values

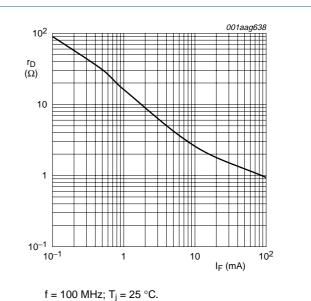
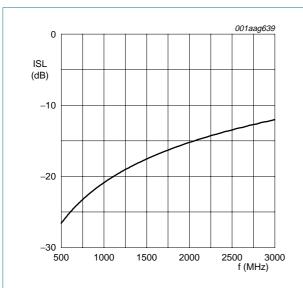


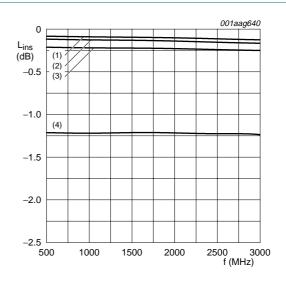
Fig 2. Forward resistance as a function of forward current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Diode zero biased and inserted in series with a 50  $\Omega$  stripline circuit





T<sub>amb</sub> = 25 °C

- (1)  $I_F = 100 \text{ mA}$
- (2)  $I_F = 10 \text{ mA}$
- (3)  $I_F = 1 \text{ mA}$
- (4)  $I_F = 0.5 \text{ mA}$

Diode inserted in series with a 50  $\Omega$  stripline circuit and biased via the analyzer Tee network

Fig 4. Insertion loss of the diode as a function of frequency; typical values



## 8. Package outline

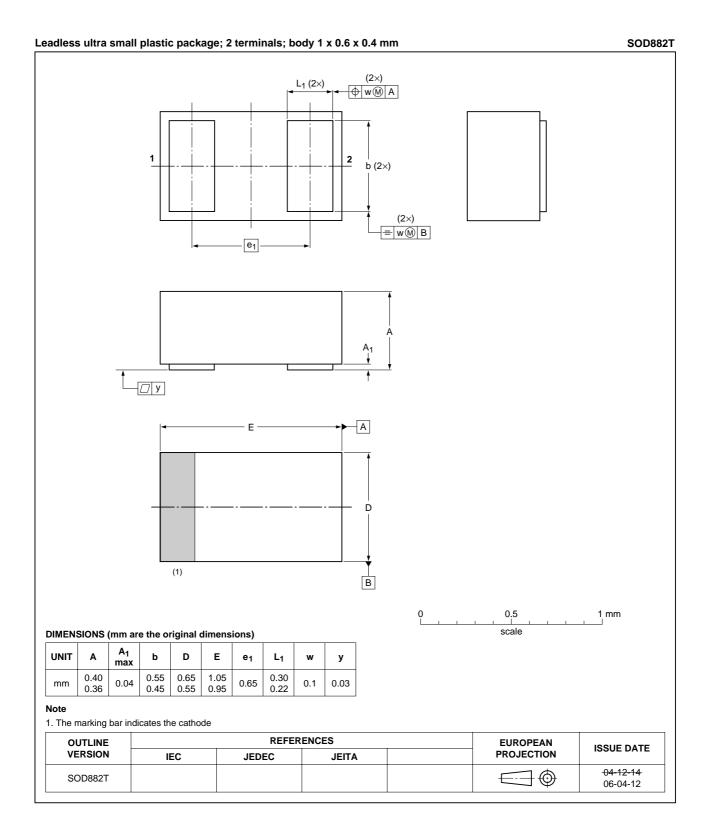


Fig 5. Package outline SOD882T

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### 9. Abbreviations

#### Table 7. Abbreviations

Acronym	Description
PIN	P-type, Intrinsic, N-type
SMD	Surface Mounted Device
RF	Radio Frequency

# 10. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP64LX_1	20070629	Product data sheet	-	-



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#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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